REMARKS

Thorough examination and careful review of the application by the Examiner is noted and appreciated.

The opportunity granted by the Examiner for a telephone interview on November 15, 2005 is further acknowledged and appreciated. During the telephone interview, the Examiner has indicated that the newly added Claim 19, which is similar to the previously canceled Claim 10, which recites the additional element of the third P-type transistor (340 in Figure 4) and the third N-type transistor (400 in Figure 4) constitute patenable features and would be favorably considered if presented in a response to the August 24, 2005 Office Action, assuming the 35 U.S.C. §112 rejections stated in a previous Office Action of March 9, 2005 is overcome.

The ground of S112 rejection for old Claim 10 in the March 9, 2005 Office Action is that the claim language in Claim 10 "a drain region of said second N-type transistor is electrically connected to a source region of said first N-type transistor" does not correspond with the drawings or the specification, furthermore, the claim language in Claim 10 "a source region of said third N-type transistor is electrically connected to a source region of said first N-type transistor and a drain region of said second N-type transistor", the Examiner stated that it cannot be determined which of transistors 360 and 380 are the first and second transistors based on the claims as worded.

The Applicants respectively submit that the claim language in old Claim 10, new Claim 19 is supported by both the drawings of Figure 4 and the specification at Page 14

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(paragraph 0026). As shown in Figure 4, the drain region 384 of the second N-type transistor 380 is connected to the source region 366 of the first N-type transistor 360. Furthermore, the source region 406 of the third N-type transistor 400 is connected to the source region 366 of the first N-type transistor 360 and the drain region 384 of the second N-type transistor 380.

The claim language in old Claim 10 is further supported by the specification at Page 14, Paragraph 0026:

"The source region 406 of the N-type transistor 400, the source region 366 of the N-type transistor 360 and the drain region 384 of the N-type transistor 380 are electrically connected together, . . ."

The Applicants therefore respectively submit that the claim language recited by the Examiner from old Claim 10 (new Claim 19) is supported by the drawings of Figure 4 and the specification at Paragraph 0026. A consideration for the allowance of the newly added Claim 19, and its dependent Claims 20-22 is respectively requested of the Examiner.

Page 7 of 8 SERIAL NO. 10/676,771 Based on the foregoing, the Applicants respectively submit that all of the pending claims, i.e. Claims 19-22 are now in condition for allowance. Such favorable action by the Examiner at an early date is respectively solicited.

In the event that the present invention as claimed is not in condition for allowance for any reason, the Examiner is respectfully invited to call the Applicants' representative at his Bloomfield Hills, Michigan office at (248) 540-4040 such that necessary action may be taken to place the application in a condition for allowance.

Respectfully submitted,

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